

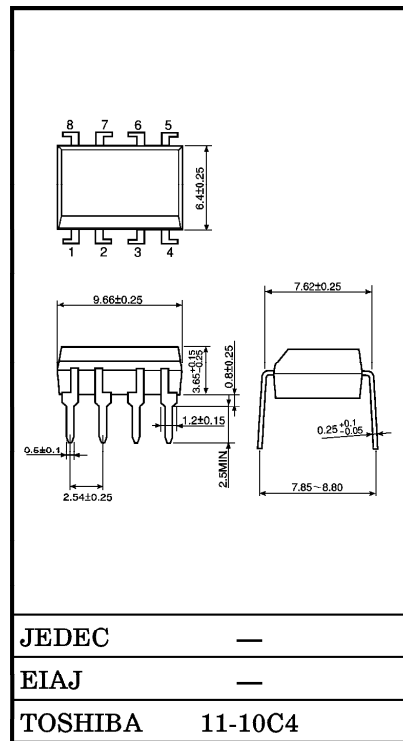
(6N135)  
 DIGITAL LOGIC ISOLATION.  
 LINE RECEIVER.  
 POWER SUPPLY CONTROL  
 SWITCHING POWER SUPPLY  
 TRANSISTOR INVERTER.

The TOSHIBA 6N135 and 6N136 consists of a high emitting diode and a one chip photo diode-transistor.

Each unit is 8-lead DIP package.

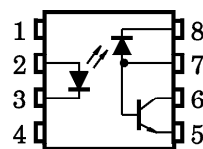
- Isolation Voltage : 2500Vrms (Min.)
- High Speed :  $t_{pHL}, t_{pLH} = 0.5\mu s$  (Typ.) ( $R_L = 1.9k\Omega$ )
- TTL Compatible
- If base pin is open, output signal will be noisy by environmental condition. For this base, TLP550 is suitable
- UL Recognized : UL1577, File No. E67349

Unit in mm

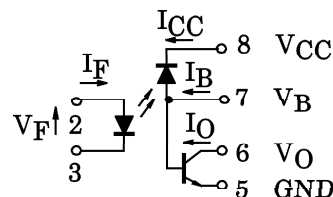


Weight : 0.54g

PIN CONFIGURATIONS



1. N.C.
2. ANODE
3. CATHODE
4. N.C.
5. EMITTER
6. COLLECTOR
7. BASE, ANODE
8. CATHODE



© The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.  
 © These TOSHIBA products are intended for use in general commercial applications (office equipment, communication equipment, measuring equipment, domestic appliances, etc.). please make sure that you consult with us before you use these TOSHIBA products in equipment which requires extraordinarily high quality and/or reliability, and in equipment which may involve life threatening or critical application, including but not limited to such uses as atomic energy control, airplane or spaceship instrumentation, traffic signals, medical instrumentation, combustion control, all types of safety devices, etc. TOSHIBA cannot accept and hereby disclaims liability for any damage which may occur in case the TOSHIBA products are used in such equipment or applications without prior consultation with TOSHIBA.

①

(6N135)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current (Note 1)	I <sub>F</sub>	25	mA
	Pulse Forward Current (Note 2)	I <sub>FP</sub>	50	mA
	Total Pulse Forward Current (Note 3)	I <sub>FPT</sub>	1	A
	Reverse Voltage	V <sub>R</sub>	5	V
	Diode Power Dissipation (Note 4)	P <sub>D</sub>	45	mW
DETECTOR	Output Current	I <sub>O</sub>	8	mA
	Peak Output Current	I <sub>OP</sub>	16	mA
	Emitter-Base Reverse Voltage (Pin 5-7)	V <sub>EB</sub>	5	V
	Supply Voltage	V <sub>CC</sub>	-0.5~15	V
	Output Voltage	V <sub>O</sub>	-0.5~15	V
	Base Current (Pin 7)	I <sub>B</sub>	5	mA
	Output Power Dissipation (Note 5)	P <sub>O</sub>	100	mW
Operating Temperature Range		T <sub>opr</sub>	-55~100	°C
Storage Temperature Range		T <sub>stg</sub>	-55~125	°C
Lead Solder Temperature (10s) (Note 6)		T <sub>sol</sub>	260	°C
Isolation Voltage (Note 7)		BV <sub>S</sub>	2500	V <sub>rms</sub>

Note 1 : Derate 0.8mA above 70°C.

Note 2 : 50% duty cycle, 1ms pulse width.  
 Derate 1.6mA/°C above 70°C.

Note 3 : Pulse width 1μs, 300pps.

Note 4 : Derate 0.9mW/°C above 70°C.

Note 5 : Derate 2mW/°C above 70°C.

Note 6 : Soldering portion of lead : up to 2mm from the body of the device.

Note 7 : R.H. ≤ 60%, AC / 1min.

(6N135)

**ELECTRICAL CHARACTERISTICS**  
**OVER RECOMMENDED TEMPERATURE ( $T_a = 0^\circ\text{C} \sim 70^\circ\text{C}$  Unless otherwise noted)**

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	※※TYP.	MAX.	UNIT
Current Transfer Ratio	6N135	CTR	$I_F = 16\text{mA}$ , $V_O = 0.4\text{V}$ $V_{CC} = 4.5\text{V}$ , $T_a = 25^\circ\text{C}$ (Note 8)	7	18	—	%
	6N136			19	24	—	%
	6N135	CTR	$I_F = 16\text{mA}$ , $V_O = 0.5\text{V}$ $V_{CC} = 4.5\text{V}$ (Note 1)	5	13	—	%
	6N136			15	21	—	%
Logic Low Output Voltage	6N135	$V_{OL}$	$I_F = 16\text{mA}$ , $I_O = 1.1\text{mA}$ $V_{CC} = 4.5\text{V}$	—	0.1	0.4	V
	6N136			$I_F = 16\text{mA}$ , $I_O = 2.4\text{mA}$ $V_{CC} = 4.5\text{V}$	—	0.1	0.4
Logic High Output Current		$I_{OH}$	$I_F = 0\text{mA}$ , $V_O = V_{CC} = 5.5\text{V}$ $T_a = 25^\circ\text{C}$	—	3	500	nA
			$I_F = 0\text{mA}$ , $V_O = V_{CC} = 15\text{V}$ $T_a = 25^\circ\text{C}$	—	0.1	1	$\mu\text{A}$
		$I_{OH}$	$I_F = 0\text{mA}$ , $V_O = V_{CC} = 15\text{V}$	—	—	50	$\mu\text{A}$
Logic Low Supply Current		$I_{CCL}$	$I_F = 16\text{mA}$ , $V_O = \text{Open}$ $V_{CC} = 15\text{V}$	—	40	—	$\mu\text{A}$
Logic High Supply Current		$I_{CCH}$	$I_F = 0\text{mA}$ , $V_O = \text{Open}$ $V_{CC} = 15\text{V}$ , $T_a = 25^\circ\text{C}$	—	0.01	1	$\mu\text{A}$
		$I_{CCH}$	$I_F = 0\text{mA}$ , $V_O = \text{Open}$ $V_{CC} = 15\text{V}$	—	—	2	$\mu\text{A}$
Input Forward Voltage		$V_F$	$I_F = 16\text{mA}$ , $T_a = 25^\circ\text{C}$	—	1.65	1.7	V
Temperature Coefficient of Forward Voltage		$\Delta V_F / \Delta T_a$	$I_F = 16\text{mA}$	—	-1.9	—	mV / °C
Input Reverse Breakdown Voltage		$BV_R$	$I_R = 10\mu\text{A}$ , $T_a = 25^\circ\text{C}$	5	—	—	V
Input Capacitance		$C_{IN}$	$f = 1\text{MHz}$ , $V_F = 0$	—	60	—	pF
Resistance (Input-Output)		$R_{I-O}$	$V_{I-O} = 500\text{V}$ (Note 9) R.H. $\leq 60\%$	—	$10^{12}$	—	$\Omega$
Capacitance (Input-Output)		$C_{I-O}$	$f = 1\text{MHz}$ (Note 9)	—	0.6	—	pF
Transistor DC Current Gain		$h_{FE}$	$V_O = 5\text{V}$ , $I_O = 3\text{mA}$	—	80	—	—

※※ All typicals at  $T_a = 25^\circ\text{C}$

(6N135)

**SWITCHING SPECIFICATIONS**

(Unless otherwise specified.  $T_a = 25^\circ\text{C}$ ,  $V_{CC} = 5\text{V}$ ,  $I_F = 16\text{mA}$ )

CHARACTERISTIC	SYMBOL	TEST CIRCUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Propagation Delay Time to Logic Low at Output	6N135	$t_{pHL}$	1	$R_L = 4.1\text{k}\Omega$	—	0.2	1.5	$\mu\text{s}$
	6N136			$R_L = 1.9\text{k}\Omega$	—	0.2	0.8	$\mu\text{s}$
Propagation Delay Time to Logic High at Output	6N135	$t_{pLH}$	1	$R_L = 4.1\text{k}\Omega$	—	1.0	1.5	$\mu\text{s}$
	6N136			$R_L = 1.9\text{k}\Omega$	—	0.5	0.8	$\mu\text{s}$
Common Mode Transient Immunity at Logic High Level Output (Note 10)	6N135	$CM_H$	2	$I_F = 0\text{mA}$ $V_{CM} = 10\text{V}_{p-p}$ $R_L = 4.1\text{k}\Omega$	—	1000	—	$\text{V} / \mu\text{s}$
	6N136			$I_F = 0\text{mA}$ $V_{CM} = 10\text{V}_{p-p}$ $R_L = 1.9\text{k}\Omega$	—	1000	—	$\text{V} / \mu\text{s}$
Common Mode Transient Immunity at Logic Low Level Output (Note 10)	6N135	$CM_L$	2	$V_{CM} = 10\text{V}_{p-p}$ $R_L = 4.1\text{k}\Omega$ $I_F = 16\text{mA}$	—	-1000	—	$\text{V} / \mu\text{s}$
	6N136			$V_{CM} = 10\text{V}_{p-p}$ $R_L = 1.9\text{k}\Omega$ $I_F = 16\text{mA}$	—	-1000	—	$\text{V} / \mu\text{s}$
Bandwidth (Note 11)	BW	—	$R_L = 100\Omega$	—	2	—	MHz	

Note 8 : DC CURRENT TRANSFER RATIO is defined as the ratio of output collector current,  $I_O$ , to the forward LED input current,  $I_F$ , times 100%.

9 : Device considered a two-terminal device : Pins 1, 2, 3, and 4 shorted together and Pins 5, 6, 7 and 8 shorted together.

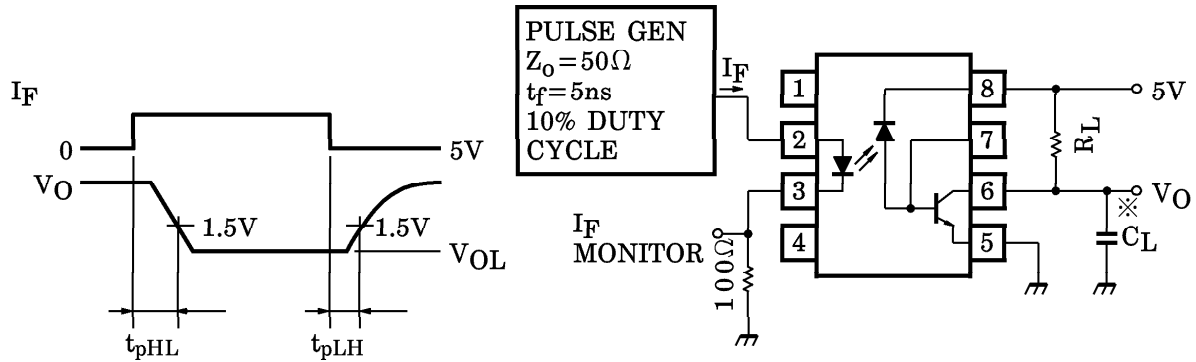
10 : Common mode transient immunity in Logic High level is the maximum tolerable (positive)  $dV_{CM}/dt$  on the leading edge of the common mode pulse,  $V_{CM}$ , to assure that the output will remain in a Logic High state (i.e.,  $V_O > 2.0\text{V}$ ).

Common mode transient immunity in Logic Low level is the maximum tolerable (negative)  $dV_{CM}/dt$  on the trailing edge of the common mode pulse signal,  $V_{CM}$ , to assure that the output will remain in a Logic Low state (i.e.,  $V_O < 0.8\text{V}$ ).

11 : The frequency at which the AC output voltage is 3dB below the low frequency asymptote.

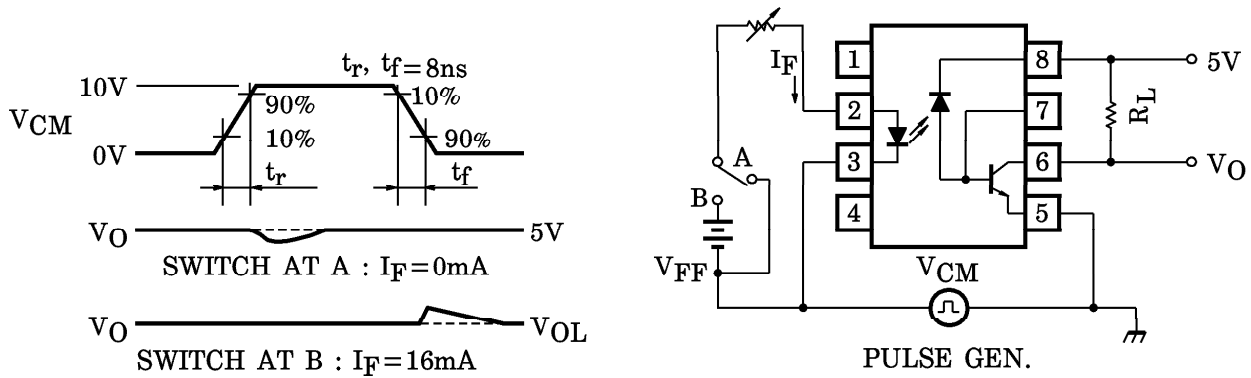
(6N135)

TEST CIRCUIT 1.

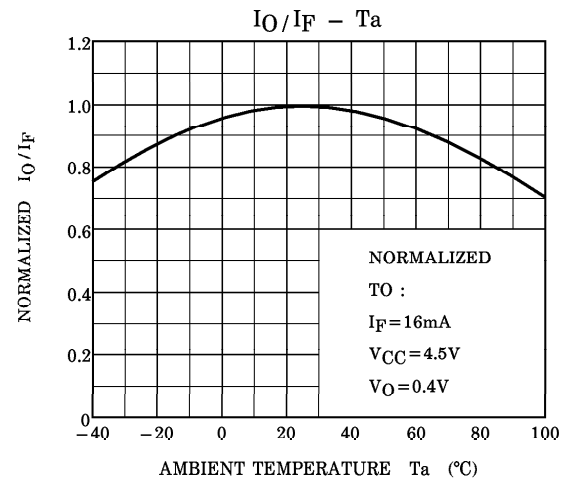
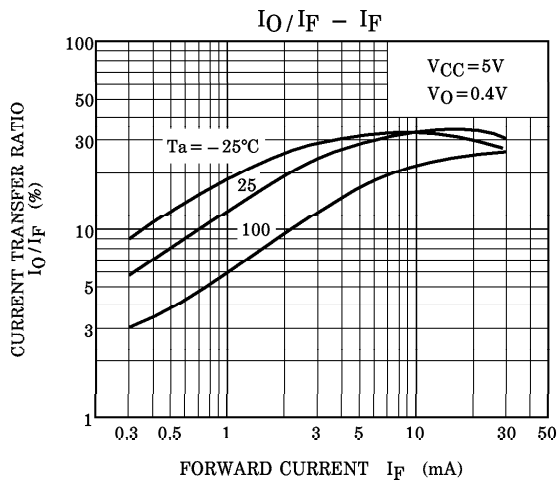
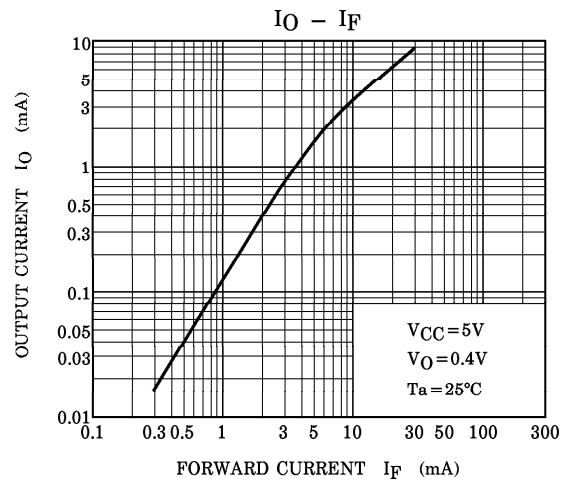
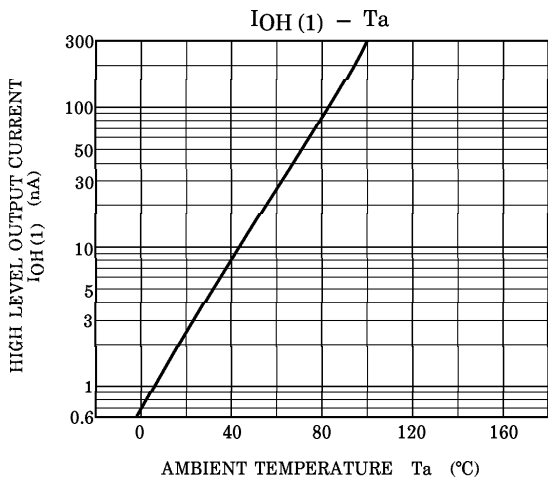
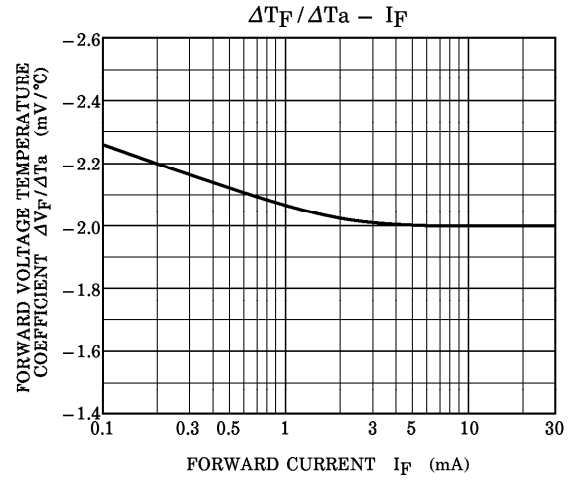
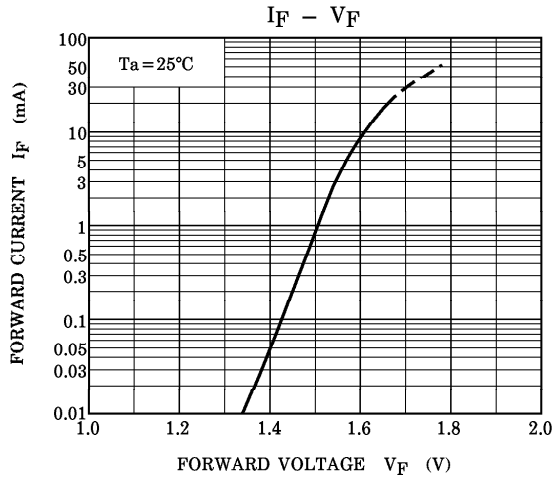


※  $C_L$  is approximately 15pF which includes probe and stray wiring capacitance.

TEST CIRCUIT 2.



(6N135)



(6N135)

